



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on)	I _D T _A = +25°C
	0.99Ω @ V _{GS} = 4.5V	0.68A
20V	1.2Ω @ V _{GS} = 2.5V	0.62A
	1.8Ω @ V _{GS} = 1.8V	0.5A
	2.4Ω @ V _{GS} = 1.5V	0.43

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- · Power management functions
- Backlighting
- Load switches

Features

- Low On-Resistance
- Low Input/Output Leakage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

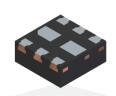
https://www.diodes.com/quality/product-definitions/

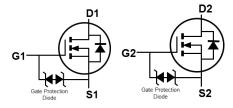
Mechanical Data

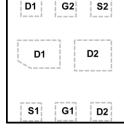
- Package: X2-DFN1010-6
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.0015 grams (Approximate)

X2-DFN1010-6 (Type UXC)









Bottom View

Equivalent Circuit

Pin-out Top View

Ordering Information (Note 4)

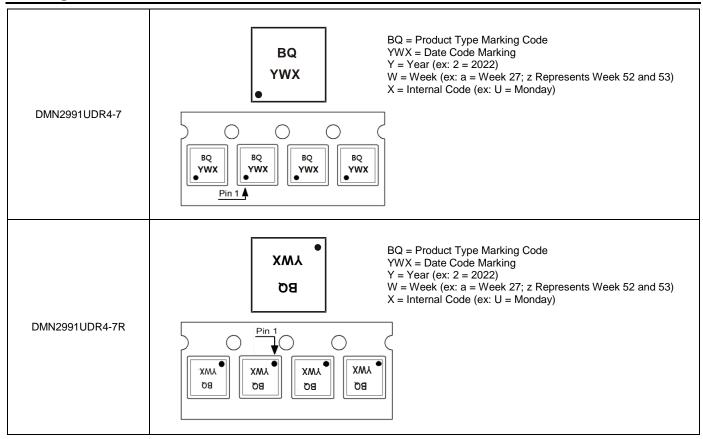
Part Number	Package	Tape Width (mm)	Tape Pitch (mm)	Packing		
Fait Nullibei	Fackage	rape widin (ililii)	Tape Fitch (IIIII)	Qty.	Carrier	
DMN2991UDR4-7	X2-DFN1010-6 (Type UXC)	8	4	5000	Tape & Reel	
DMN2991UDR4-7R	X2-DFN1010-6 (Type UXC)	8	4	5000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information



Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	Vgss	±8	V		
Continuous Drain Current (Note 5) VGS = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	lo	0.5 0.4	А
Maximum Continuous Body Diode Forward Current (Is	0.4	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	1.4	Α		

Thermal Characteristics

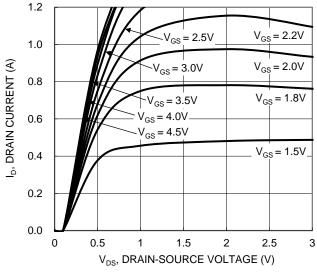
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	331	°C/W
Total Power Dissipation (Note 6)		PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	180	°C/W
Operating and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	°C

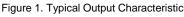
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	V _G S = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	Igss	1		±10	μΑ	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		1	0.5	0.99		V _{GS} = 4.5V, I _D = 100mA
Static Drain-Source On-Resistance	R _{DS(ON)}	1	0.6	1.2	Ω	V _{GS} = 2.5V, I _D = 50mA
Static Drain-Source On-Resistance		_	0.7	1.8		V _{GS} = 1.8V, I _D = 20mA
		_	0.9	2.4		$V_{GS} = 1.5V, I_D = 10mA$
Diode Forward Voltage	VsD	_	0.8	1.0	V	V _G S = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	14.6	_		
Output Capacitance	Coss	_	4.7	_	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	3.2	_		1 - 1.0001112
Total Gate Charge	Qg	_	0.28	_		
Gate-Source Charge	Qgs	_	0.04	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V$ $I_{D} = 250mA$
Gate-Drain Charge	Qgd	_	0.1	_		ID = 230IIIA
Turn-On Delay Time	td(ON)		7.1	_		
Turn-On Rise Time	t _R		18	_		V _{DD} = 10V, V _{GS} = 4.5V
Turn-Off Delay Time	t _{D(OFF)}	_	125	_	ns	$R_L = 47\Omega$, $R_G = 10\Omega$ $I_D = 200 \text{mA}$
Turn-Off Fall Time	tF	1	56.9	_		15 - 2001174

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







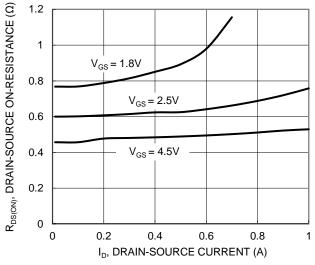


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

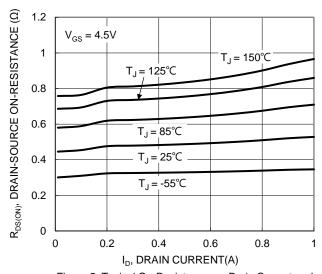


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

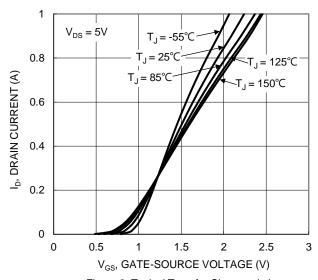


Figure 2. Typical Transfer Characteristic

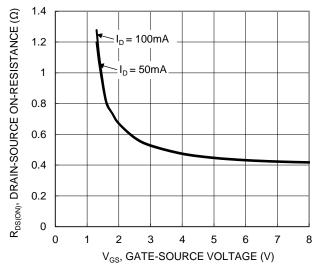


Figure 4. Typical Transfer Characteristic

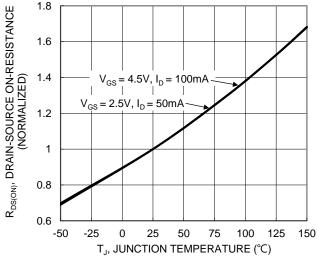


Figure 6. On-Resistance Variation with Junction Temperature



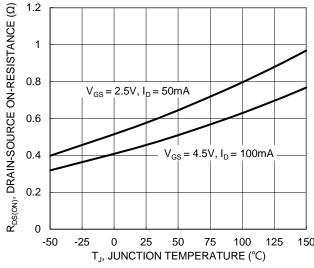


Figure 7. On-Resistance Variation with Junction Temperature

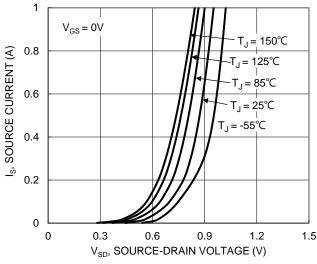


Figure 9. Diode Forward Voltage vs. Current

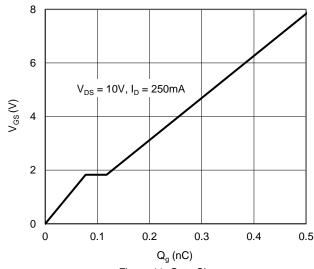


Figure 11. Gate Charge

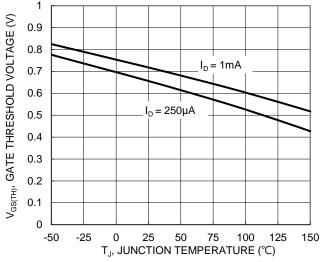


Figure 8. Gate Threshold Variation vs. Junction Temperature

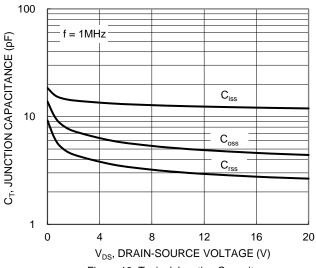


Figure 10. Typical Junction Capacitance

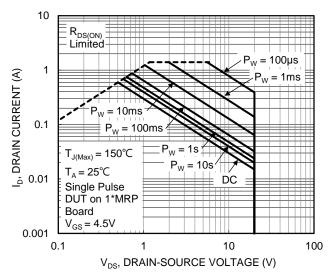


Figure 12. SOA, Safe Operation Area



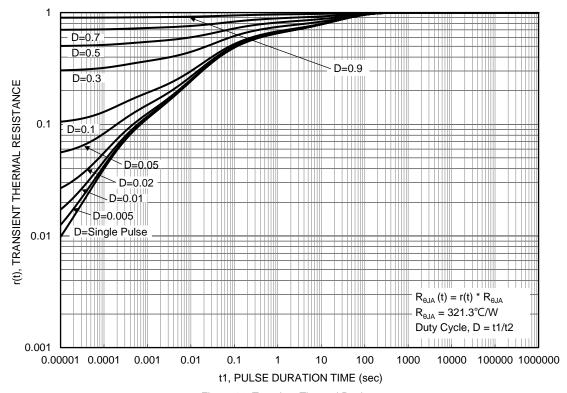


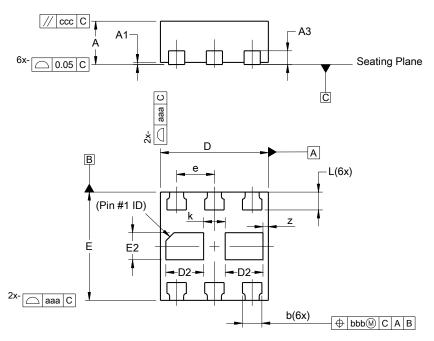
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-6 (Type UXC)

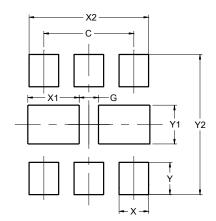


	X2-DFN1010-6						
	(Type	UXC)					
Dim	Min	Max	Тур				
Α	-	0.40	0.39				
A1	-	0.05					
A3			0.127				
b	0.13	0.23	0.18				
D	0.95	1.05	1.00				
D2	0.30	0.40	0.35				
Е	0.95	1.05	1.00				
E2	0.20	0.30	0.25				
е	0.	350 BS	С				
L	0.115	0.215	0.165				
k			0.20				
Z	0.02	0.08	0.05				
aaa	0.08						
bbb	0.07						
CCC		0.05					
All	Dimensi	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-6 (Type UXC)



Dimensions	Value
Dillielisions	(in mm)
С	0.700
G	0.300
X	0.230
X1	0.450
X2	0.930
Y	0.250
Y1	0.300
Y2	1.085



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